

TOSHIBA Transistor Silicon NPN Epitaxial Type

2SC5376F

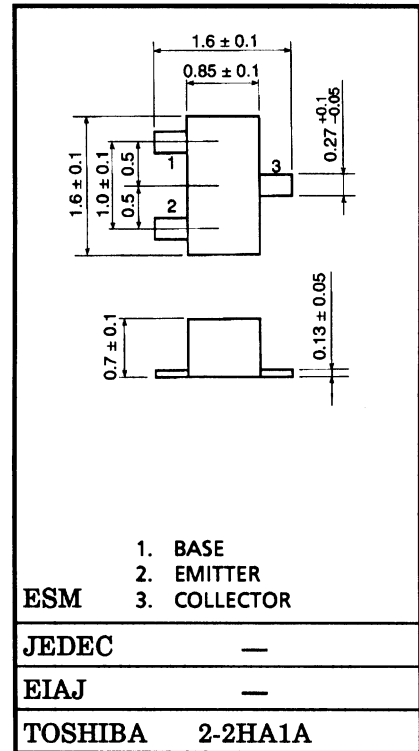
Audio Frequency General Purpose Amplifier Applications
For Muting and Switching Applications

- Low Collector Saturation Voltage: $V_{CE(sat)}(1) = 15 \text{ mV (typ.)}$
@ $I_C = 10 \text{ mA}/I_B = 0.5 \text{ mA}$
- High Collector Current: $I_C = 400 \text{ mA (max)}$

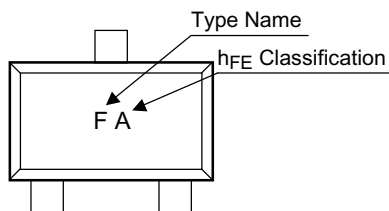
Maximum Ratings (Ta = 25°C)

Characteristics	Symbol	Rating	Unit
Collector-base voltage	V_{CBO}	15	V
Collector-emitter voltage	V_{CEO}	12	V
Emitter-base voltage	V_{EBO}	5	V
Collector current	I_C	400	mA
Base current	I_B	50	mA
Collector power dissipation	P_C	100	mW
Junction temperature	T_j	125	°C
Storage temperature range	T_{stg}	-55 to 125	°C

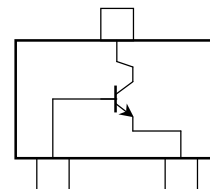
Unit in mm



Marking



Equivalent Circuit (top view)



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Electrical Characteristics (Ta = 25°C)

Characteristics		Symbol	Test Condition	Min	Typ.	Max	Unit
Collector cut-off current		I_{CBO}	$V_{CB} = 15\text{ V}, I_E = 0$	—	—	0.1	μA
Emitter cut-off current		I_{EBO}	$V_{EB} = 5\text{ V}, I_C = 0$	—	—	0.1	μA
DC current gain		h_{FE} (Note)	$V_{CE} = 2\text{ V}, I_C = 10\text{ mA}$	300	—	1000	
Collector-emitter saturation voltage		$V_{CE(sat)}(1)$	$I_C = 10\text{ mA}, I_B = 0.5\text{ mA}$	—	15	30	mV
		$V_{CE(sat)}(2)$	$I_C = 200\text{ mA}, I_B = 10\text{ mA}$	—	110	250	mV
Base-emitter voltage		$V_{BE(sat)}$	$I_C = 200\text{ mA}, I_B = 10\text{ mA}$	—	0.87	1.2	V
Transition frequency		f_T	$V_{CE} = 2\text{ V}, I_C = 10\text{ mA}$	80	130	—	MHz
Collector output capacitance		C_{ob}	$V_{CB} = 10\text{ V}, I_E = 0, f = 1\text{ MHz}$	—	4.2	—	pF
Collector-emitter on resistance		R_{on}	$I_B = 1\text{ mA}, V_{in} = 1\text{ V}_{rms}, f = 1\text{ kHz}$	—	0.9	—	Ω
Switching time	Turn-on time	t_{on}	<p>Duty Cycle $\leq 2\%$ $I_{B1} = -I_{B2} = 5\text{ mA}$</p>	—	85	—	ns
	Storage time	t_{stg}		—	170	—	ns
	Fall time	t_f		—	40	—	ns

Note: h_{FE} Classification A: 300 to 600, B: 500 to 1000

